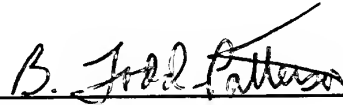




Applicant believes that no fee is due as a result of this filing. However, If the Commissioner deems that fees are due under 37 CFR § 1.17(p) pursuant to § 1.97, he is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to Deposit Account No. 20-0782/AMAT 6551/CMI/TICL/RKK.

Respectfully submitted,



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U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)		Docket No. AMAT/6551/CMI/TICL/ RKK	Serial No. 10/033,544
INFORMATION DISCLOSURE STATEMENT BY APPLICATION		Applicant Hytros, et al.	Confirmation No.: 7363
(Use several sheets if necessary)		Filing Date December 27, 2001	Group Unknown
Examiner:			

## U.S. Patent Documents

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A1	6,200,844	03/13/2001	Huang	438	238	02/12/1999
	A2	6,148,761	11/21/2000	Majewski et al.	118	715	12/09/1998
	A3	6,086,677	07/11/2000	Umotoy et al.	118	715	06/16/1998
	A4	5,970,378	10/19/1999	Shue et al.	438	656	07/23/1997
	A5	5,956,595	09/21/1999	Zenke	438	398	07/15/1997
	A6	5,871,586	02/16/1999	Crawley et al.	118	715	04/09/1997
	A7	5,665,640	09/09/1997	Foster et al.	438	680	06/03/1994
	A8	5,576,071	11/19/1996	Sandhu	427	534	11/08/1994
	A9	5,567,483	10/22/1996	Foster et al.	427	535	06/05/1995
	A10	5,308,655	05/03/1994	Eichman et al.	427	248.1	02/10/1992
	A11	5,279,857	01/18/1994	Eichman et al.	427	255	08/16/1991

## F reign Patent Documents

*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
	B1	63-22984	09/26/1988	JP	H01L	12/28	<input type="checkbox"/>	<input type="checkbox"/>
	B2	0711846	05/15/1996	EP	C23C	16/34	<input type="checkbox"/>	<input type="checkbox"/>

## OTHER ART

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	Arena, et al., "A New Low Temperature PECVD TiN Compatible With Multilevel Vias Application", VMIC Conference, pp. 566-71, June 18-20, 1996
	C2	Allendorf, et al., "Chemical Vapor Deposition", Proceedings of the Fourteenth International Conference and EUROCV D-11, Vol. 97-25, pp. 1625-33.
	C3	Konecni, et al., "A Stable Plasma Treated CVD Titanium Nitride Film for Barrier/Glue Layer Applications", VMIC Conference, pp. 181-3.
	C4	Kim, et al., "Effect of N <sub>2</sub> /H <sub>x</sub> Plasma Treatment on the Properties of TiN Films Prepared by Chemical Vapor Deposition from TiCl <sub>4</sub> and NH <sub>3</sub> ", Jap. J. Appl. Phys., Vol. 38, Part 2, No. 4B, pp. L461-3, April 15, 1999
	C5	USSN 09/978,140, Zhang, et al., "Method of Titanium and Titanium Nitride Layer Deposition, filed October 15, 2001

Examiner

Date Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.